

Bias Resistor Transistor

NPN Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

LDTTC124TLT1G

- **Applications**

Inverter, Interface, Driver

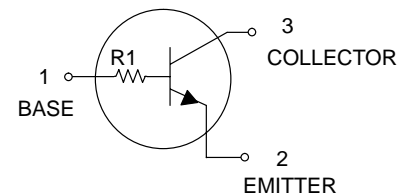
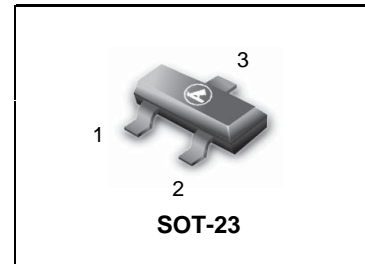
- **Features**

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.

- **Absolute maximum ratings** ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CB0}	50	V
Collector-emitter voltage	V_{CE0}	50	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_c	100	mA
Collector power dissipation	P_c	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTTC124TLT1G	H4	22	—	3000/Tape & Reel
LDTTC124TLT3G	H4	22	—	10000/Tape & Reel

- **Electrical characteristics** ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CB0}	50	—	—	V	$I_c=50\mu\text{A}$
Collector-emitter breakdown voltage	BV_{CE0}	50	—	—	V	$I_c=1\text{mA}$
Emitter-base breakdown voltage	BV_{EB0}	5	—	—	V	$I_E=50\mu\text{A}$
Collector cutoff current	I_{cB0}	—	—	0.5	μA	$V_{CB}=50\text{V}$
Emitter cutoff current	I_{EB0}	—	—	0.5	μA	$V_{EB}=4\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_c/I_B=5\text{mA}/0.5\text{mA}$
DC current transfer ratio	h_{FE}	100	250	600	—	$V_{CE}=5\text{V}$, $I_c=1\text{mA}$
Input resistance	R_1	15.4	22	28.6	$\text{k}\Omega$	—
Transition frequency	f_T *	—	250	—	MHz	$V_{CE}=10\text{V}$, $I_E=-5\text{mA}$, $f=100\text{MHz}$

* Characteristics of built-in transistor

LDTC124TLT1G

● **Electrical characteristic curves**

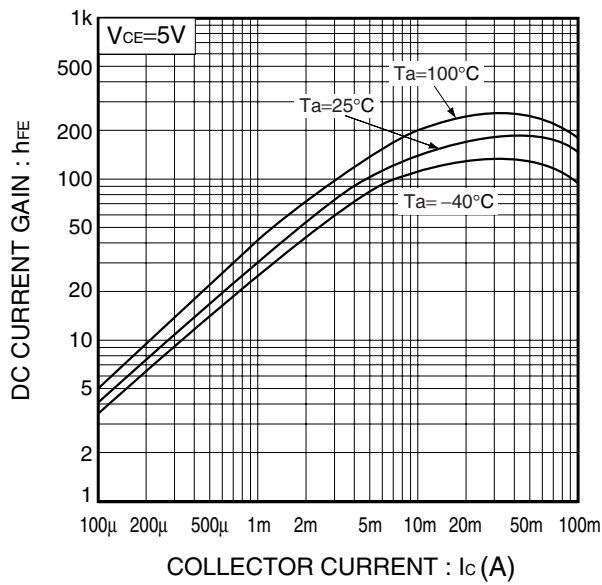


Fig.1 DC current gain vs. Collector current

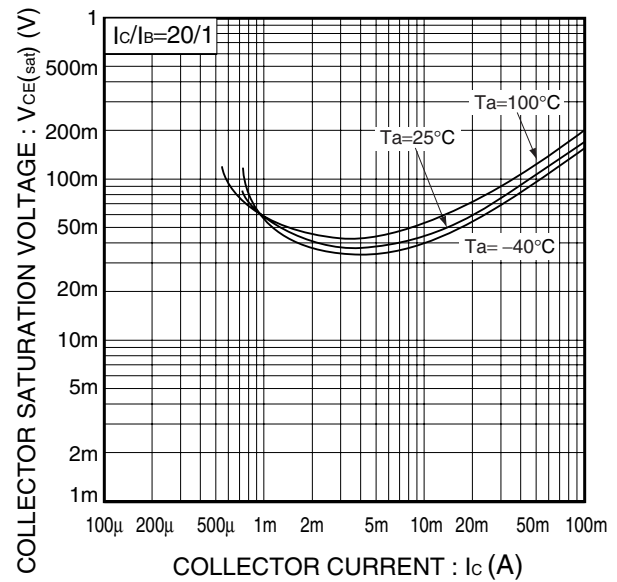


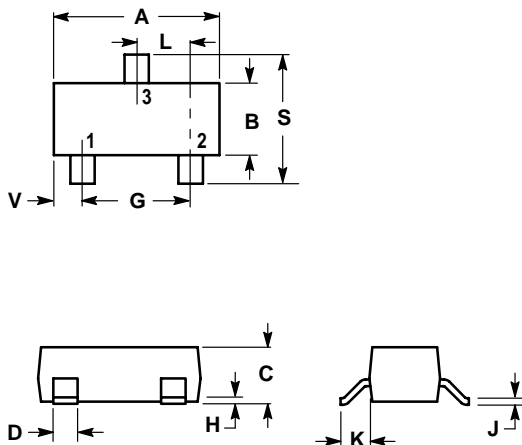
Fig.2 Collector-Emitter saturation voltage vs. Collector current

LDT C124TLT1G

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

